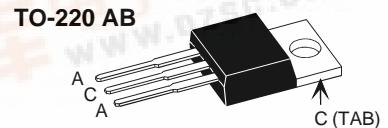
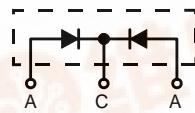




Power Schottky Rectifier with common cathode

$I_{FAV} = 2 \times 10 A$
 $V_{RRM} = 45 V$
 $V_F = 0.45 V$

| V_{RSM} | V_{RRM} | Type |
|-----------|-----------|---------------|
| V | V | |
| 45 | 45 | DSSK 20-0045B |



A = Anode, C = Cathode , TAB = Cathode

| Symbol | Conditions | Maximum Ratings | |
|----------------|--|-----------------|------------|
| I_{FRMS} | | 35 | A |
| I_{FAV} | $T_c = 135^\circ C$; rectangular, $d = 0.5$ | 10 | A |
| I_{FAV} | $T_c = 135^\circ C$; rectangular, $d = 0.5$; per device | 20 | A |
| I_{FSM} | $T_{VJ} = 45^\circ C$; $t_p = 10$ ms (50 Hz), sine | 160 | A |
| E_{AS} | $I_{AS} = 13 A$; $L = 180 \mu H$; $T_{VJ} = 25^\circ C$; non repetitive | 24 | mJ |
| I_{AR} | $V_A = 1.5 \cdot V_{RRM}$ typ.; $f=10$ kHz; repetitive | 1.3 | A |
| $(dv/dt)_{cr}$ | | 1000 | V/ μ s |
| T_{VJ} | | -55...+150 | °C |
| T_{VJM} | | 150 | °C |
| T_{stg} | | -55...+150 | °C |
| P_{tot} | $T_c = 25^\circ C$ | 75 | W |
| M_d | mounting torque | 0.4...0.6 | Nm |
| Weight | typical | 2 | g |

| Symbol | Conditions | Characteristic Values | |
|------------|--|-----------------------|------|
| | | typ. | max. |
| I_R | ① $T_{VJ} = 25^\circ C$ $V_R = V_{RRM}$ $T_{VJ} = 100^\circ C$ $V_R = V_{RRM}$ | 5 | mA |
| | | 50 | mA |
| V_F | $I_F = 10 A$; $T_{VJ} = 125^\circ C$ $I_F = 10 A$; $T_{VJ} = 25^\circ C$ $I_F = 20 A$; $T_{VJ} = 125^\circ C$ | 0.45 0.51 0.70 | V |
| R_{thJC} | | 1.7 | K/W |
| R_{thCH} | | 0.5 | K/W |

Features

- International standard package
- Very low V_F
- Extremely low switching losses
- Low I_{RM} -values
- Epoxy meets UL 94V-0

Applications

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Dimensions see outlines.pdf

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

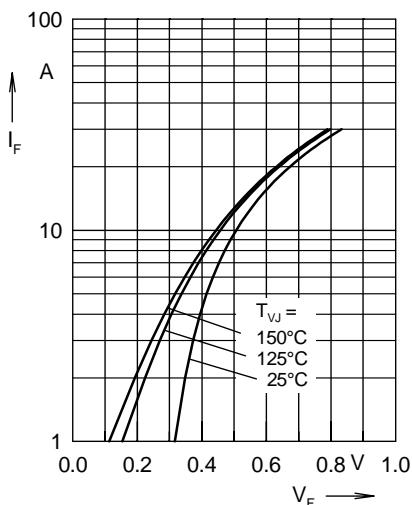


Fig. 1 Maximum forward voltage drop characteristics

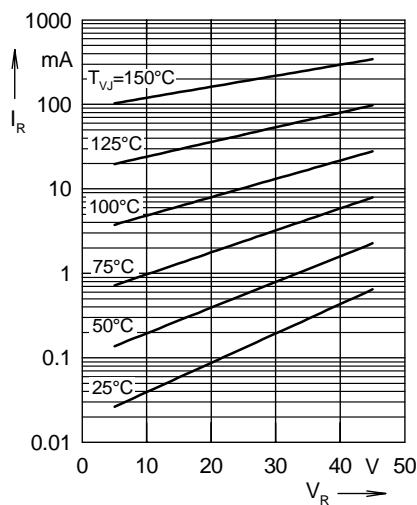


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

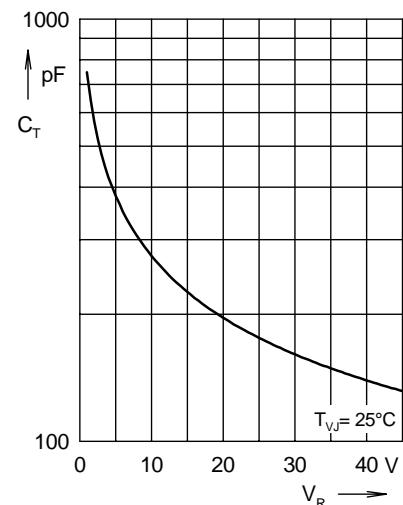


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

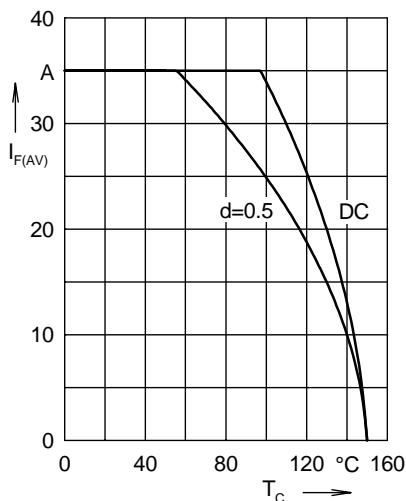


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

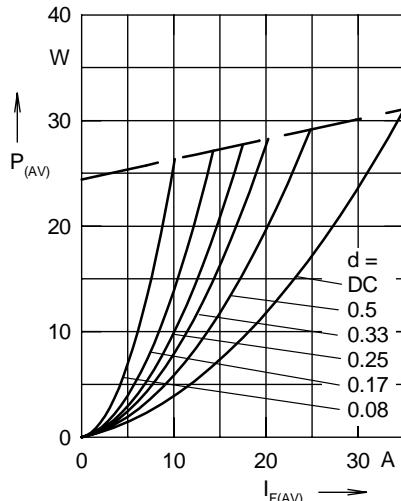


Fig. 5 Forward power loss characteristics

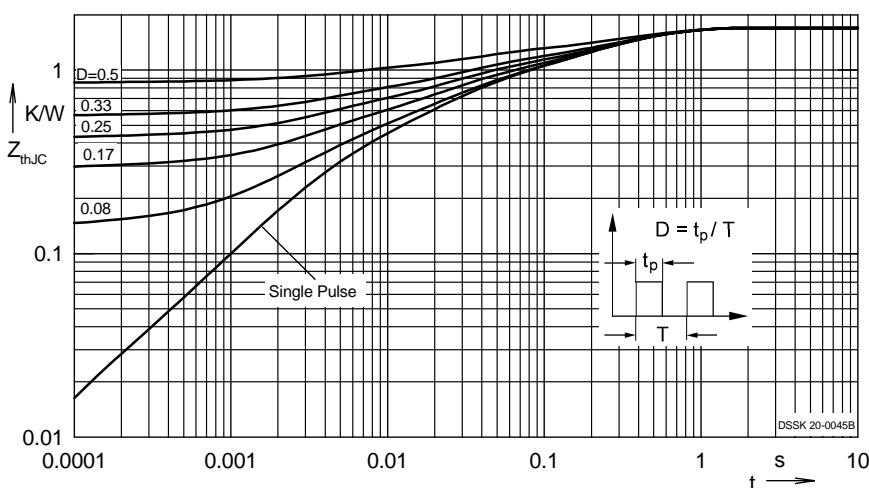


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode